Solution to Exercise 3.2-1"Crystal Identity"

The jump rate of a vacancy is identical to that of an atom next to the vacancy. It was given by

$$\lor = \lor_0 \cdot \exp{-\frac{G_m}{kT}} \approx \lor_0 \cdot \exp{-\frac{H_m}{kT}}$$

 \bigcirc The time t_a needed so that all the atoms with a vacancy next to them will make one jump thus is

$$t_{a} = \frac{1}{-} = \frac{1}{-} \cdot \exp \frac{H_{m}}{-}$$

$$\vee \quad \vee_{0} \qquad kT$$

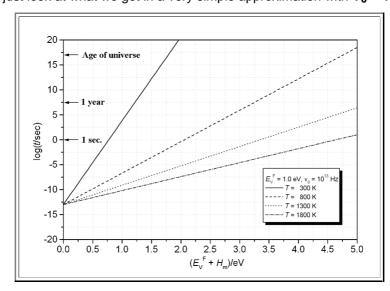
- After that time ta, the fraction of all atoms that had a vacancy a a neighbor, has made one jump.
 - If you now wait another t_a , a second set of atoms can now make a jump. This second set may include atoms from the first set which simply jump back to their old position, but we ignore this effect for a rough estimate.
 - If all atoms of the crystal are supposed to make one jump, you have to wait for a time t_c that is a defined multiple of t_a. It is simply

$$t_{\rm c} = m \cdot t_{\rm a} = \frac{t_{\rm a}}{c_{\rm V}}$$

- Because the multiplier m is of course the inverse of the vacancy concentration $c_V = \exp{-(H_F)/kT}$
- fc is the quantity we we are looking for, it is

$$t_{C} = \frac{1}{-} \cdot \exp \frac{H_{m}}{kT} \cdot \exp \frac{H_{F}}{kT} = \frac{1}{-} \cdot \exp \frac{H_{m} + H_{F}}{kT} = \frac{1}{-} \cdot \exp \frac{H_{SD}}{kT}$$

- With H_{SD} = enthalpy of self diffusion.
- We <u>may replace</u> $1/v_0$ by $1/v_0 = g \cdot a^2/D_{SD}$ and use the diffusion coefficient for self-diffusion to obtain values for specific materials, but lets just look at what we get in a very simple approximation with $v_0 = 10^{13}$ Hz



- Shown is t_c on a (rather far-reaching) log scale versus $H_m + H_F = H_{SD}$, i.e. the self-diffusion enthalpy H_{SD} , with the temperature as a parameter.
 - For $H_{\rm m} + H_{\rm F} = 0$, $t_{\rm C}$ is $10^{-13} \, \rm s$ as it should be.

- For sensible values. e.g. H_{SD} = 2 eV, you must be very patient at room temperature, but at 800 °C, your crystal has a different identity after 1 second! Take Si, with H_{SD} ≈ 5 eV and a melting point of roughly 1700 K, and again no atom will be where it was after a rather short time.
- Using better values for v_0 from the self-diffusion coefficient as stated above, just shifts the whole set of curves a "little bit" on the t- axis and thus t_0 by the same (logarithmic) amount